

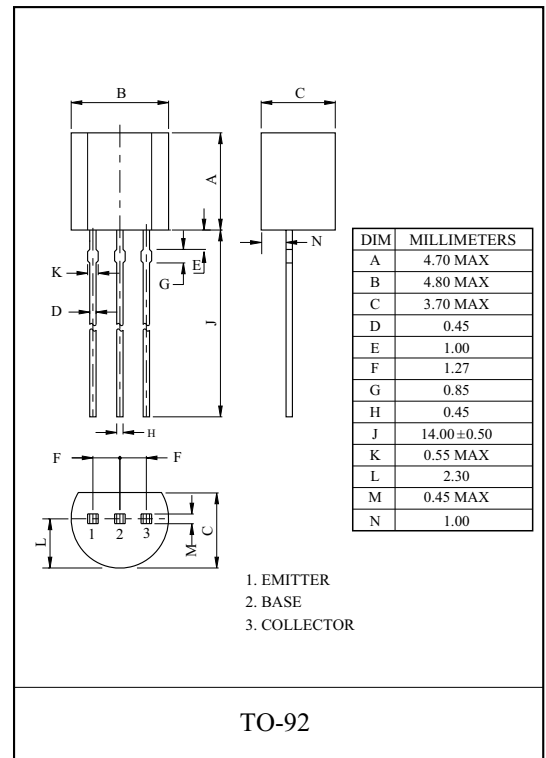
HIGH CURRENT APPLICATION.

**FEATURE**

- Complementary to KTC8050.

**MAXIMUM RATING (Ta=25 )**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	-35	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-30	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	I <sub>C</sub>	-800	mA
Emitter Current	I <sub>E</sub>	800	mA
Collector Power Dissipation	P <sub>C</sub>	625	mW
Junction Temperature	T <sub>j</sub>	150	
Storage Temperature Range	T <sub>stg</sub>	-55 150	



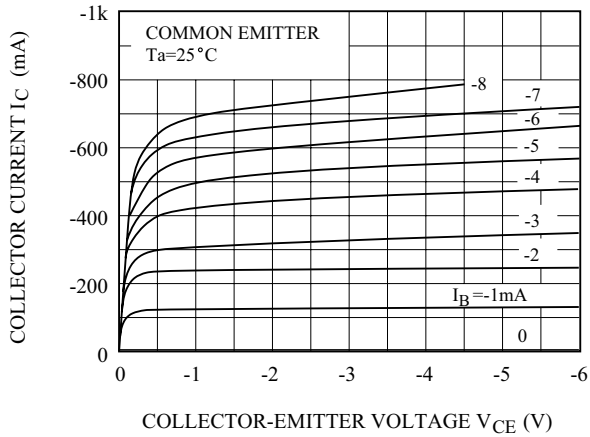
**ELECTRICAL CHARACTERISTICS (Ta=25 )**

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> =-15V, I <sub>E</sub> =0	-	-	-50	nA
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-0.5mA, I <sub>E</sub> =0	-35	-	-	V
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-30	-	-	V
DC Current Gain	h <sub>FE</sub> (1) (Note)	V <sub>CE</sub> =-1V, I <sub>C</sub> =-50mA	100	-	300	
	h <sub>FE</sub> (2)	V <sub>CE</sub> =-1V, I <sub>C</sub> =-350mA	60	-	-	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA	-	-	-0.5	V
Base-Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-500mA	-	-	-1.2	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-10mA	-	120	-	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, f=1MHz, I <sub>E</sub> =0	-	19	-	pF

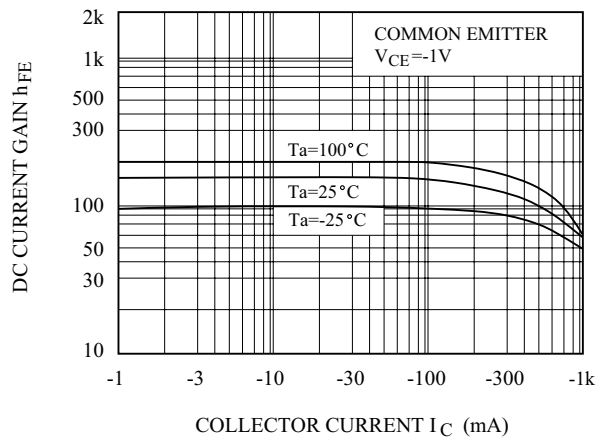
Note : h<sub>FE</sub>(1) Classification C : 100 200, D : 150 300

# KTC8550

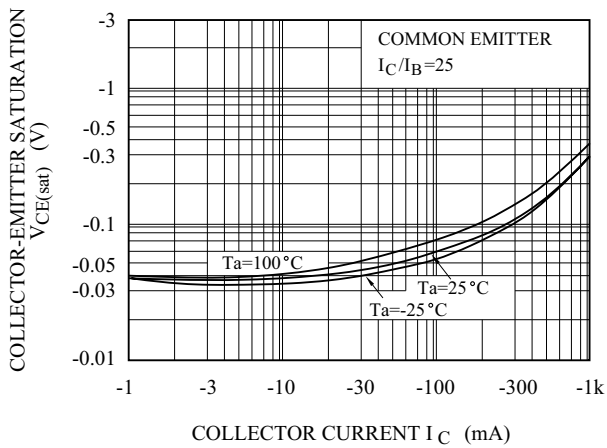
$I_C - V_{CE}$



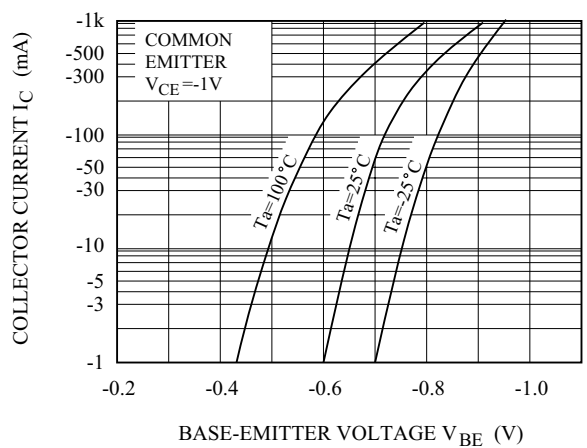
$h_{FE} - I_C$



$V_{CE(sat)} - I_C$



$I_C - V_{BE}$



$P_c - T_a$

